

Title (en)

UPROM memory cell having a structure compatible with the manufacture of table cloth matrices of EPROM memory cells with self-aligned lines of source and drain, and process for its manufacture.

Title (de)

UPROM-Speicherzelle mit einer Struktur, die kompatibel ist mit der Herstellung von Tischdecken-Matrizen von EPROM-Speicherzellen mit selbstausrichtenden Linien von Source und Drain, und Verfahren zu ihrer Herstellung.

Title (fr)

Cellule de mémoire UPROM ayant une structure compatible avec la fabrication de matrices en forme de nappe de cellules de mémoires EPROM à lignes de source et de drain auto-alignées et son procédé de fabrication.

Publication

**EP 0392587 A2 19901017 (EN)**

Application

**EP 90200785 A 19900402**

Priority

IT 2008389 A 19890410

Abstract (en)

The UPROM memory cell comprises self-aligned lines of source (5) and lines of drain (4) obtained in a semiconductor substrate (1). It also comprises a strip of floating gate (7), a strip of dielectric (8) and a strip of barrier polysilicon (9), each of these strips (7, 8, 9) being provided with a respective pair of small lateral fins (10, 11, 12). The UPROM cell lastly comprises a control gate (13) superimposed over and self-aligned with the floating gate (7).

IPC 1-7

**H01L 27/115**; **H01L 29/788**

IPC 8 full level

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